

阮弼群

著作目錄

期刊論文

1. P.C. Juan, K.C. Lin, H.Y. Chu, Y.C. Kuo, H.W. Wang, T.Y. Shih (2017, Jun). Ferroelectric of HfO₂ dielectric layer sputtered with TiN or ZrN for sandwich-like metal-insulator-metal capacitors. *Microelec. Rel.*, in press. (Accepted).
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專書論文

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2. 阮弼群 (2011 年 09 月)。第 10 章作者 非揮發性記憶體製程。書名: **新世代積體電路製程技術** (ISBN: 978-957-483-671-0) (pp. 331-368)。鄭晃忠教授主編, 台灣電子材料與元件協會編著, 東華書局出版。國科會: 99-2221-E-131-022-MY2。